

SCT2080KE

N-channel SiC power MOSFET

V _{DSS}	1200V
R _{DS(on)} (Typ.)	$80 \text{m}\Omega$
I _D	40A
PD	262W

Features

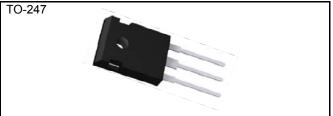
- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

Application

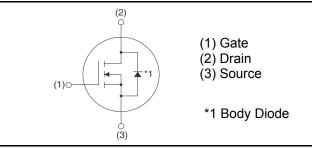
- Solar inverters
- DC/DC converters
- Induction heating
- Motor drives

•Absolute maximum ratings (T_a = 25°C)

•Outline



Inner circuit



Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Tuno	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	С
	Marking	SCT2080KE

Parameter		Symbol	Value	Unit
Drain - Source voltage		V _{DSS}	1200	V
$T_c = 25^{\circ}C$		I _D ^{*1}	40	А
Continuous drain current	$T_c = 100^{\circ}C$	I _D ^{*1}	28	А
Pulsed drain current		I _{D,pulse} *2	80	А
Gate - Source voltage (DC)		V _{GSS}	-6 to 22	V
Gate - Source surge voltage (T _{surge} < 300nsec)		V _{GSS-surge} *3	-10 to 26	V
Power dissipation ($T_c = 25^{\circ}C$)		P _D	262	W
Junction temperature		Tj	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

•Thermal resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	0.44	0.57	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

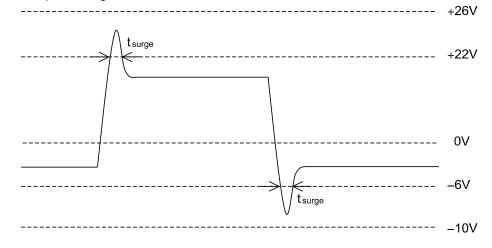
•Electrical characteristics ($T_a = 25^{\circ}C$)

Parameter	Symbol	Conditions		Unit		
Faranielei	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 1mA	1200	-	-	V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 1200V, V_{GS} = 0V$ $T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$	-	1 2	10 -	μΑ
Gate - Source leakage current	I_{GSS^+}	V_{GS} = +22V, V_{DS} = 0V	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	V_{GS} = -6V, V_{DS} = 0V	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4.4$ mA	1.6	2.8	4.0	V

*1 Limited only by maximum temperature allowed.

*2 PW \leq 10 $\mu s,$ Duty cycle \leq 1%

*3 Example of acceptable Vgs waveform



*4 Pulsed

•Electrical characteristics ($T_a = 25^{\circ}C$)

Parameter	Symbol	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		V _{GS} = 18V, I _D = 10A				
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	T _j = 25°C	-	80	117	mΩ
		T _j = 125°C	-	125	-	
Gate input resistance	R _G	f = 1MHz, open drain	-	6.3	-	Ω
Transconductance	${\sf g}_{\sf fs}$	V _{DS} = 10V, I _D = 10A	-	3.7	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	2080	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	77	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	16	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V V _{DS} = 0V to 500V	-	116	-	pF
Turn - on delay time	t _{d(on)} *4	V _{DD} = 400V, V _{GS} = 18V	-	35	-	
Rise time	t _r *4	I _D = 10A	-	36	-	20
Turn - off delay time	t _{d(off)} *4	R _L = 40Ω	-	76	-	ns
Fall time	t _f *4	$R_{G} = 0\Omega$	-	22	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 600V, I_{D} = 10A$ $V_{GS} = 18V/0V$	-	174	-	
Turn - off switching loss	E _{off} *4	R _G = 0Ω, L=500μH *E _{on} includes diode reverse recovery	-	51	-	μJ

●Gate Charge characteristics (T_a = 25°C)

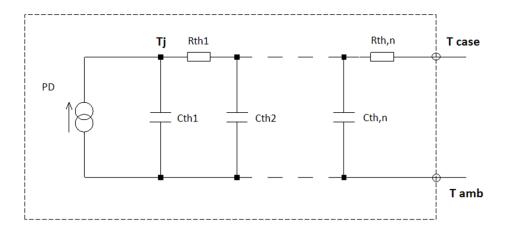
Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Q_g^{*4}	V _{DD} = 400V	-	106	-	
Gate - Source charge	${\sf Q_{gs}}^{*4}$	I _D = 10A	-	27	-	nC
Gate - Drain charge	Q_{gd}^{*4}	V _{GS} = 18V	-	31	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 400V, I_D = 10A$	-	9.7	-	V

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions		Values		Unit	
Faranieter	Symbol Conditions –		Min.	Тур.	Max.		
Inverse diode continuous, forward current	ا _S *1	T _c = 25°C	-	-	40	А	
Inverse diode direct current, pulsed	I _{SM} *2	T _c - 20 0	-	-	80	А	
Forward voltage	V_{SD} *4	V _{GS} = 0V, I _S = 10A	-	4.6	-	V	
Reverse recovery time	t _{rr} *4		-	31	-	ns	
Reverse recovery charge	Q _{rr} ^{*4}	I _F = 10A, V _R = 400V di/dt = 150A/μs	-	44	-	nC	
Peak reverse recovery current	^{*4}		-	2.3	-	А	

•Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	0.078		C_{th1}	0.005	
R _{th2}	0.197	K/W	C_{th2}	0.018	Ws/K
R _{th3}	0.162		$C_{\text{th}3}$	0.249	



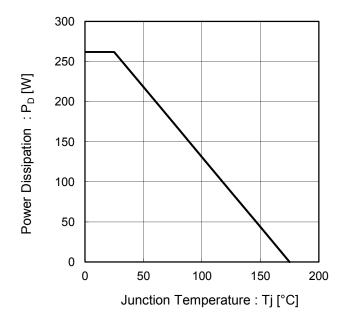


Fig.1 Power Dissipation Derating Curve

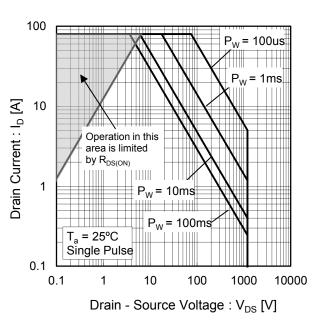
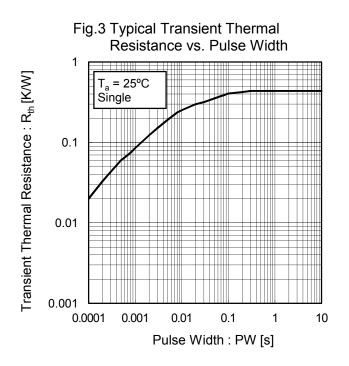


Fig.2 Maximum Safe Operating Area



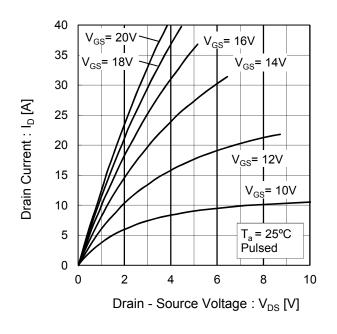


Fig.4 Typical Output Characteristics(I)

Fig.5 Typical Output Characteristics(II)

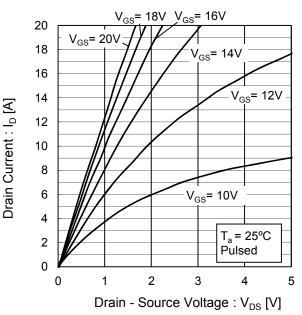
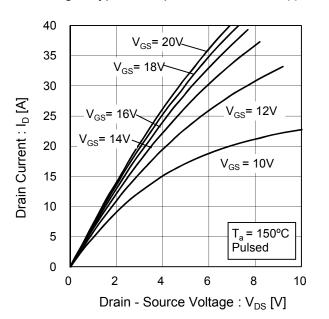
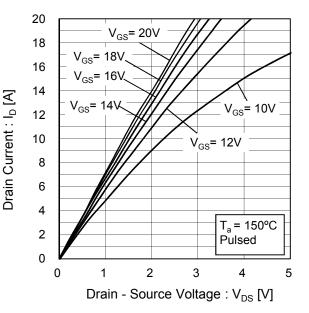


Fig.6 Typical Output Characteristics(I)

Fig.7 Typical Output Characteristics(II)





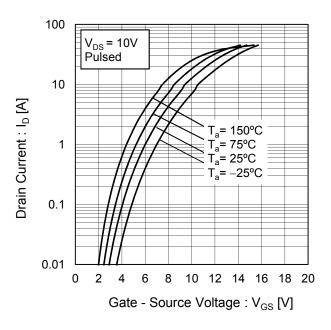


Fig.8 Typical Transfer Characteristics

Fig.9 Typical Transfer Characteristics (II)

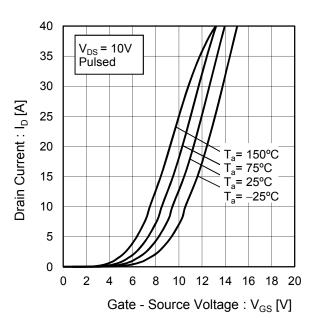
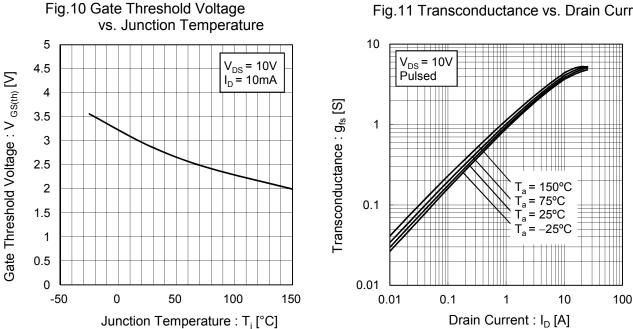


Fig.11 Transconductance vs. Drain Current



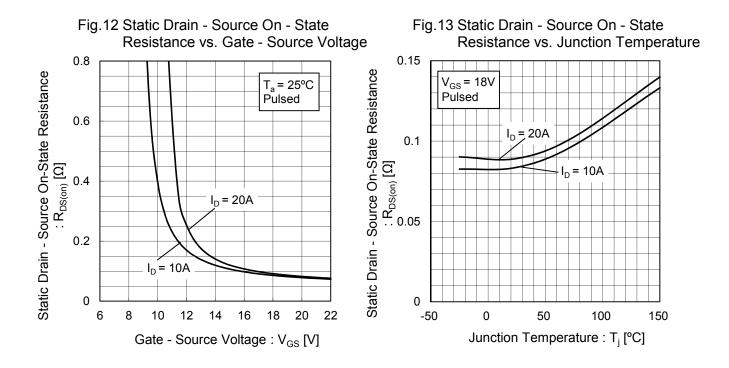


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current 1 Static Drain - Source On-State Resistance V_{GS} = 18V Pulsed : R_{DS(on)} [Ω] T_a = 150°C T_a[−] = 75°C T_a = 25°C T_a[−]= −25°C 0.01 0.1 1 10 100 Drain Current : I_D [A]

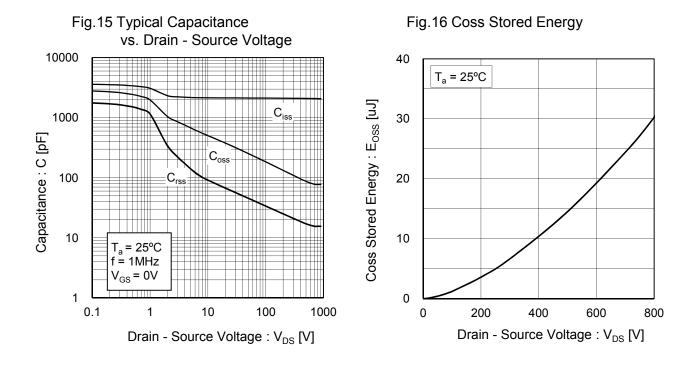
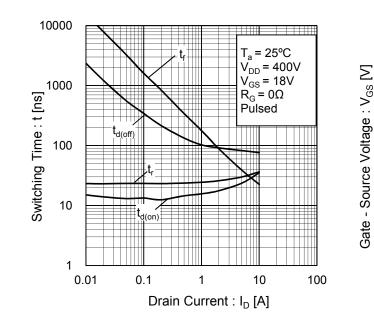
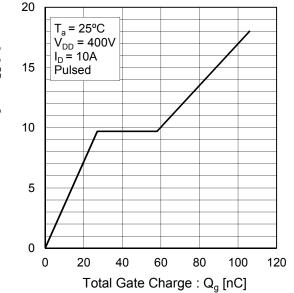


Fig.17 Switching Characteristics

Fig.18 Dynamic Input Characteristics





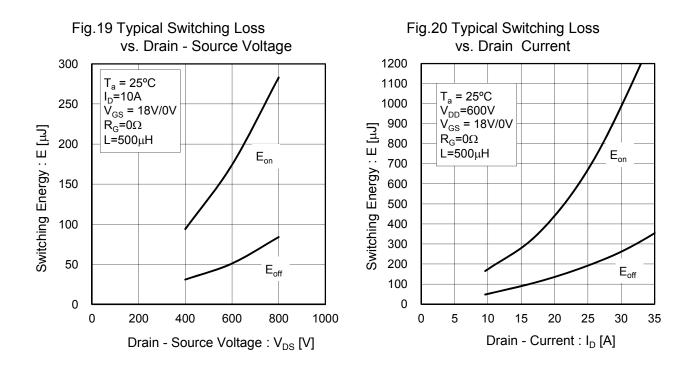
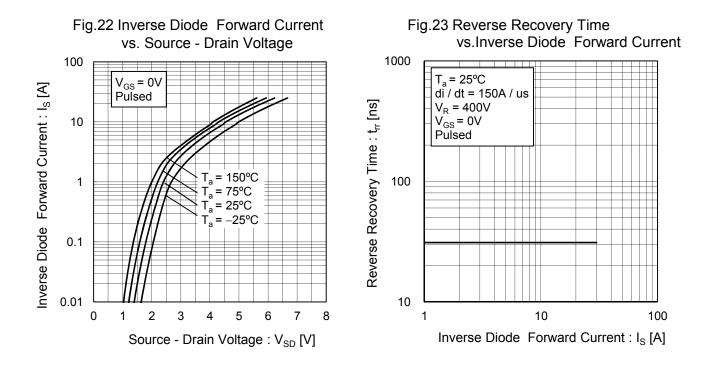


Fig.21 Typical Switching Loss vs. External Gate Resistance 500 T_a = 25°C 450 V_{DD}=600V 400 I_D=10A V_{GS} = 18V/0V L=500μH Switching Energy : E [µJ] 350 Eon 300 250 200 150 $\mathsf{E}_{\mathsf{off}}$ 100 50 0 5 0 10 15 20 30 25 External Gate Resistance : $R_G [\Omega]$



Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

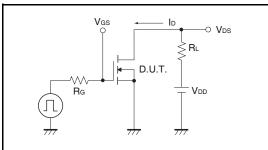


Fig.2-1 Gate Charge Measurement Circuit

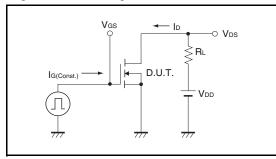


Fig.3-1 Switching Energy Measurement Circuit

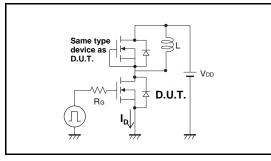


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

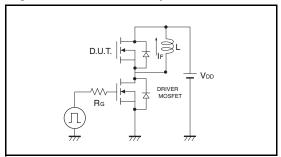


Fig.1-2 Switching Waveforms

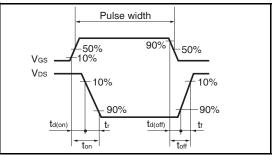


Fig.2-2 Gate Charge Waveform

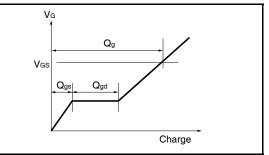
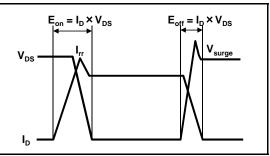
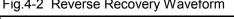
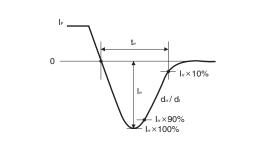


Fig.3-2 Switching Waveforms







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